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Patent Application No. 10/755,498  
Customer Number: 42717

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Applicant:	Bor-Wen Chan	§	Docket No.:	24061.605
		§		(TSMC2001-0714C)
Serial No.:	10/755,498	§		
		§	Examiner:	Deo, Duy Vu Nguyen
Filing Date:	January 12, 2004	§		
		§	Art Unit:	1765
For:	Method of Forming a Stacked	§		
	Capacitor Structure with Increased	§	Conf. No.:	1284
	Surface Area for a DRAM Device	§		
		§		

**RESPONSE TO RESTRICTION REQUIREMENT**

Mail Stop: Amendment  
Commissioner for Patents  
PO Box 1450  
Alexandria, VA 22313-1450

Dear Sir:

In response to the Office Action mailed March 7, 2005, applicant hereby elects Group II, Claims 28-35, which is drawn to a product, classified in class 257, subclass 213.

An early action on the merits is respectfully requested.

Respectfully submitted,

David M. O'Dell  
Reg. No. 42,044

Date: 3-16-05

HAYNES AND BOONE, LLP  
901 Main Street, Suite 3100  
Dallas, Texas 75202-3789  
Telephone: 972-739-8635  
Facsimile: 214-200-0853

**CERTIFICATE OF MAILING**

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Mail Stop: Amendment, Commissioner For Patents, PO Box 1450, Alexandria, VA 22313-1450 on the date below.

Julie A. Curtis  
Name

3/17/05  
Date